MOSFETs Silicon N-channel MOS (U-MOSIX-H)

# TPHR6503PL

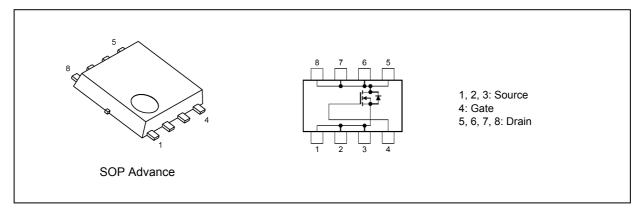
#### 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators

#### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 30 \text{ nC}$  (typ.)
- (3) Small output charge:  $Q_{oss} = 81.3 \text{ nC}$  (typ.)
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 0.41 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (5) Low leakage current:  $I_{DSS}$  = 10  $\mu$ A (max) ( $V_{DS}$  = 30 V)
- (6) Enhancement mode:  $V_{th}$  = 1.1 to 2.1 V ( $V_{DS}$  = 10 V,  $I_D$  = 1.0 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25$ °C unless otherwise specified)

Characteris	tics		Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	30	V
Gate-source voltage		(Note 1)	V <sub>GSS</sub>	±20	
Drain current (DC)	(T <sub>c</sub> = 25 °C)	(Note 2)	Ι <sub>D</sub>	150	A
Drain current (DC)	(Silicon limit)	(Note 2), (Note 3)	Ι <sub>D</sub>	393	A
Drain current (pulsed)	(t = 100 μs)	(Note 2)	I <sub>DP</sub>	500	A
Power dissipation	(T <sub>c</sub> = 25 °C)		PD	170	W
Power dissipation		(Note 4)	PD	3.0	W
Power dissipation		(Note 5)	PD	0.96	W
Single-pulse avalanche energy		(Note 6)	E <sub>AS</sub>	374	mJ
Single-pulse avalanche current		(Note 6)	I <sub>AS</sub>	120	A
Channel temperature			T <sub>ch</sub>	175	°C
Storage temperature			T <sub>stg</sub>	-55 to 175	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	(T <sub>c</sub> = 25 °C)		R <sub>th(ch-c)</sub>	0.88	°C/W
Channel-to-ambient thermal resistance	(T <sub>a</sub> = 25 °C)	(Note 4)	R <sub>th(ch-a)</sub>	50	
Channel-to-ambient thermal resistance	(T <sub>a</sub> = 25 °C)	(Note 5)	R <sub>th(ch-a)</sub>	156	

Note 1: +20V /-16V ensured at DC condition.

-20V ensured at pulse condition(duty 5%).

Note 2: Ensure that the channel temperature does not exceed 175  $^\circ \text{C}.$ 

Note 3: Limited by silicon chip capability. Package limit is 150 A.

Note 4: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 5: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 6:  $V_{DD}$  = 24 V,  $T_{ch}$  = 25 °C (initial), L = 0.02 mH,  $I_{AS}$  = 120 A

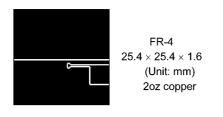
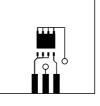
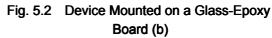


Fig. 5.1 Device Mounted on a Glass-Epoxy

Board (a)



FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2oz copper



Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

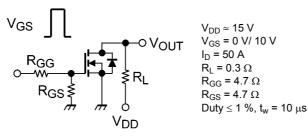
#### 6. Electrical Characteristics

#### 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V	_	_	±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	30		—	V
	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	15	_	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 mA	1.1	_	2.1	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 50 A	_	0.6	0.89	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A		0.41	0.65	

#### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	7700	10000	рF
Reverse transfer capacitance	C <sub>rss</sub>		_	220	—	
Output capacitance	C <sub>oss</sub>		_	2720	_	
Gate resistance	r <sub>g</sub>	—	_	0.6	1.1	Ω
Switching time (rise time)	tr	See Fig. 6.2.1	_	12	—	ns
Switching time (turn-on time)	t <sub>on</sub>		_	36	—	
Switching time (fall time)	t <sub>f</sub>	]	_	10	_	
Switching time (turn-off time)	t <sub>off</sub>		_	100	_	



#### Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

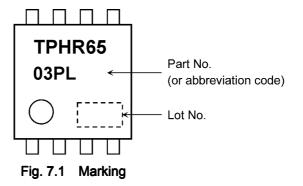
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD}\approx 15~V,~V_{GS}\text{ = }10~V,~I_{D}\text{ = }50~A$	_	110	_	nC
gate-drain)		$V_{DD} \approx 15$ V, $V_{GS}$ = 4.5 V, $I_D$ = 50 A	_	52	_	
Gate-source charge 1	Q <sub>gs1</sub>	$V_{DD} \approx 15$ V, $V_{GS}$ = 10 V, $I_D$ = 50 A	_	24	_	
Gate-drain charge	Q <sub>gd</sub>		—	16	_	
Gate switch charge	Q <sub>SW</sub>		_	30	_	
Output charge	Q <sub>oss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	81.3	_	

#### 6.4. Source-Drain Characteristics ( $T_a = 25 \ ^{\circ}C$ unless otherwise specified)

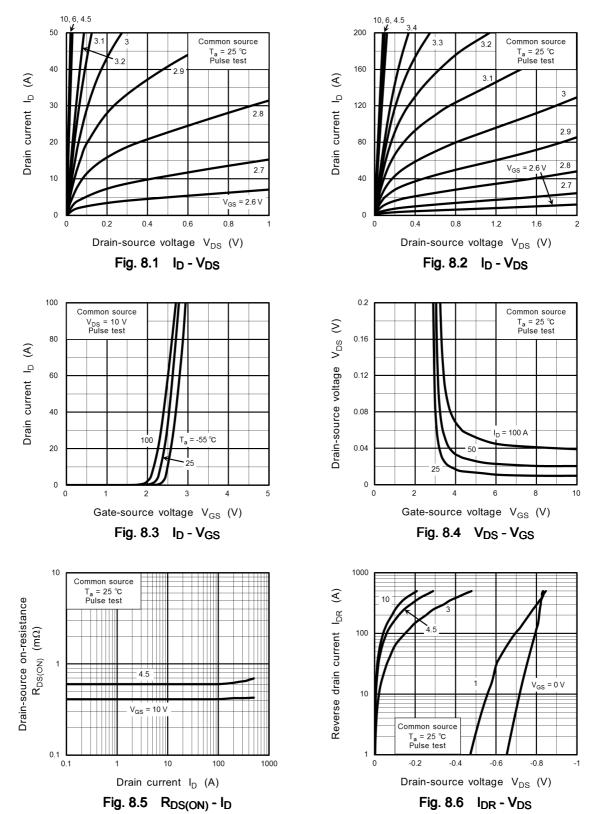
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 7)	I <sub>DRP</sub> (t = 100 μs)	_	—		500	A
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 150 A, V <sub>GS</sub> = 0 V			-1.2	V
Reverse recovery time		V <sub>R</sub> = 15 V, I <sub>DR</sub> = 37.5 A, V <sub>GS</sub> =	_	59	—	ns
Reverse recovery charge	Q <sub>rr</sub>	0 V, -dl <sub>DR</sub> /dt = 100 A/μs	_	70	_	nC

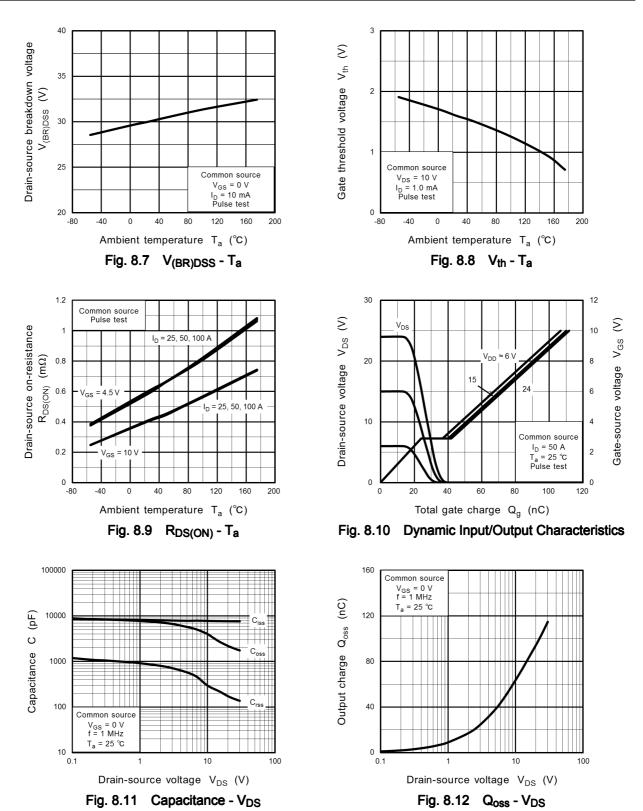
Note 7: Ensure that the channel temperature does not exceed 175 °C.

### 7. Marking

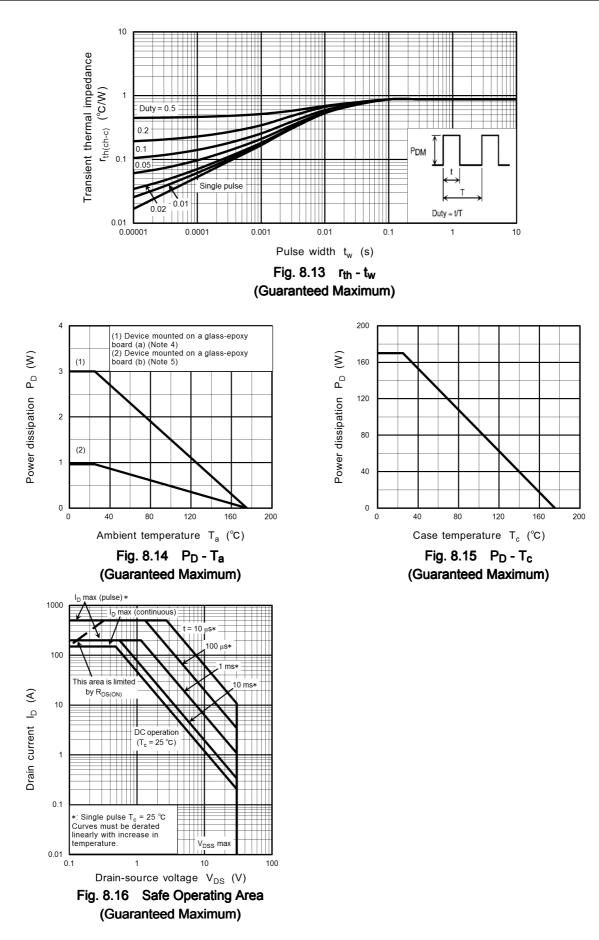


#### 8. Characteristics Curves (Note)





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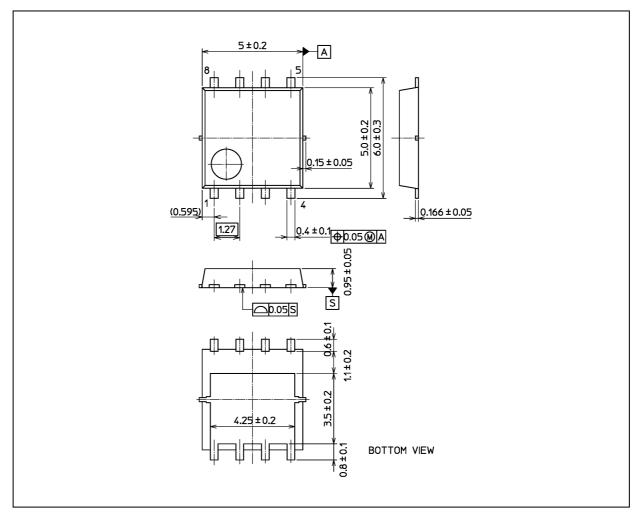
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### TPHR6503PL

#### **Package Dimensions**

Unit: mm



Weight: 0.069 g (typ.)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

Package Name(s)

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